μPD4362B
16,384 x 4-Bit
Static CMOS RAM

Description

The μPD4362B is a 16,384-word by 4-bit static RAM fabricated with advanced silicon-gate technology. A unique design using CMOS peripheral circuits and N-channel memory cells with polysilicon resistors makes the μPD4362B a high-speed device that requires very low power and no clock or refreshing.

The μPD4362B is packaged in a standard 22-pin plastic DIP and 24-pin plastic SOJ.

Features

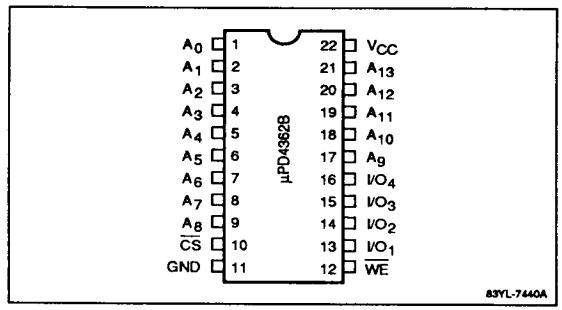
- Single + 5-volt power supply
- Fully static operation—no clock or refreshing
- TTL-compatible inputs and outputs
- Common I/O capability
- Standard 300-mil, 22-pin plastic DIP and 24-pin plastic SOJ packaging

Ordering Information

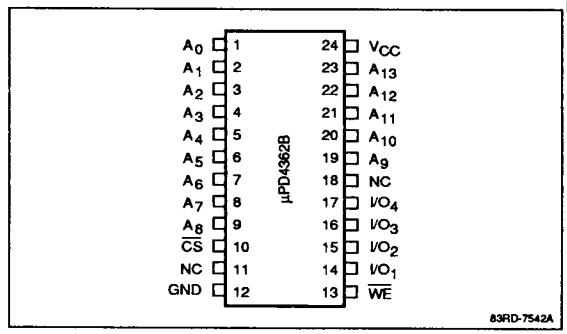
Part Number	Access Time (max)	Package
μPD4362BCR-12	12 ns	22-pin plastic DIP
CR-15	15 ns	
CR-20	20 ns	
μPD4362BLA-12	12 ns	24-pin plastic SOJ
LA-15	15 ns	
LA-20	20 ns	

Pin Configuration

22-Pin Plastic DIP



24-Pin Plastic SOJ



Pin Identification

Symbol	Function
A_0 - A_{13}	Address inputs
I/O_1 - I/O_4	Data inputs and outputs
$\overline{CS}$	Chip select
$\overline{WE}$	Write enable
GND	Ground
V_{CC}	+5-volt power supply
NC	No connection

Absolute Maximum Ratings

Supply voltage, V_{CC}	−0.5 to +7.0 V
Input and output voltages, V_{IN} (Note 1)	−0.5 to V_{CC} + 0.5 V
Operating temperature, T_{OPR}	0 to +70°C
Storage temperature, T_{STG}	−55 to +125°C
Power dissipation, P_D	1.0 W

Exposure to Absolute Maximum Ratings for extended periods may affect device reliability; exceeding the ratings could cause permanent damage. The device should be operated within the limits specified under DC and AC Characteristics.

Notes:

(1) V_{IN} = −3.0 V for 10 ns pulse.

Truth Table

Function	$\overline{CE}$	$\overline{WE}$	Input/Output	I_{CC}
Not selected	H	X	High-Z	Standby
Read	L	H	D_{OUT}	Active
Write	L	L	D_{IN}	Active

Notes:

(1) X = don't care.

Capacitance

T_A = 25°C; f = 1 MHz (Note 1); V_{IN} and V_{DOUT} = 0 V

Parameter	Symbol	Min	Typ	Max	Unit
Input capacitance	C_{IN}			6	pF
Output capacitance	C_{DOUT}			8	pF

Notes:

(1) This parameter is sampled and not 100% tested.

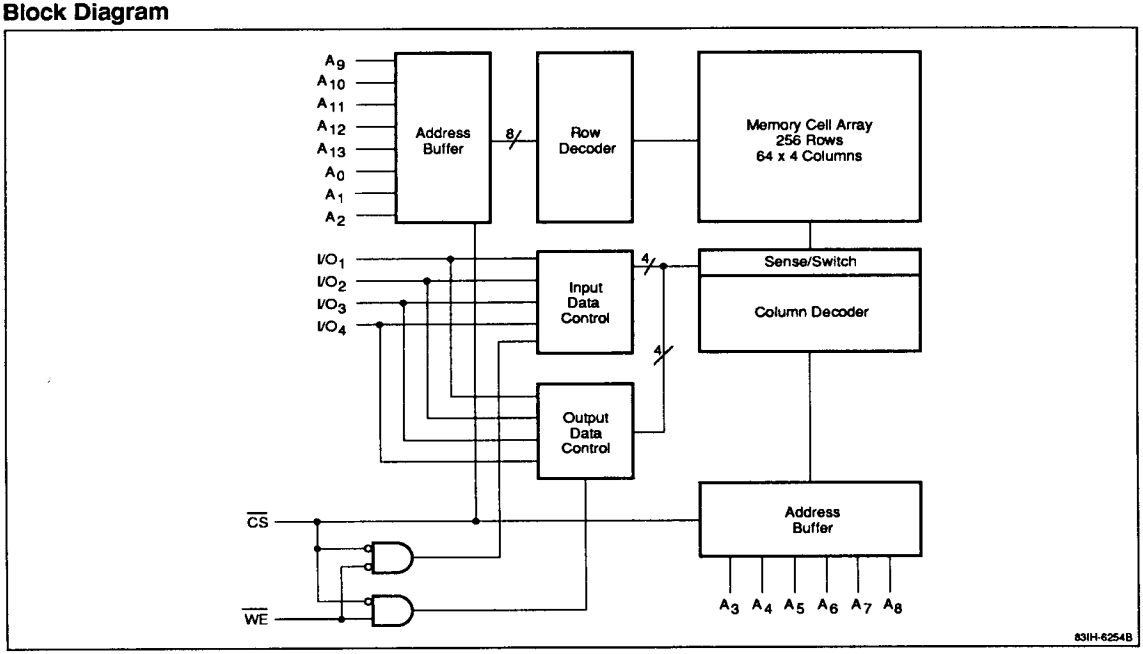
Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
Input voltage, high	V_{IH}	2.2		V_{CC} + 0.3	V
Input voltage, low	V_{IL}	−0.5		0.8	V
Operating temperature	T_A	0		70	°C

Notes:

(1) V_{IL} = −3.0 V for 10 ns pulse.

Block Diagram



DC Characteristics

T_A = 0 to +70°C; V_{CC} = +5.0 V ±10%

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Input leakage current	I_{LI}	−2		2	μA	V_{IN} = 0 V to V_{CC}; V_{CC} = max
Output leakage current	I_{LO}	−2		2	μA	V_{OUT} = 0 V to V_{CC}; $\overline{CS}$ = V_{IH}; V_{CC} = max
Standby supply current	I_{SB}			20	mA	$\overline{CS}$ = V_{IH}
	I_{SB1}			2	mA	$\overline{CS}$ ≥ V_{CC} − 0.2 V; V_{IN} ≤ 0.2 V or ≥ V_{CC} − 0.2 V
Output voltage, low	V_{OL}			0.4	V	I_{OL} = 8.0 mA
Output voltage, high	V_{OH}	2.4			V	I_{OH} = −4.0 mA

AC Characteristics

T_A = 0 to +70°C; V_{CC} = +5.0 V ±10%

		μPD4362B-12		μPD4362B-15		μPD4362B-20			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Test Conditions
Read Operation									
Operating supply current	I_{CC}		130		120		110	mA	$\overline{CS}$ = V_{IL}; I_{DOUT} = 0 mA
Read cycle time	t_{RC}	12		15		20		ns	(Note 2)
Address access time	t_{AA}		12		15		20	ns	
Chip selection access time	t_{ACS}		12		15		20	ns	
Output hold from address change	t_{OH}	2		3		3		ns	
Chip selection to output to low-Z	t_{LZ}	2		3		3		ns	(Note 3)
Chip deselection to output to high-Z	t_{HZ}	0	7	0	7	0	8	ns	(Note 4)
Chip selection to power-up time	t_{PU}	0		0		0		ns	
Chip deselection to power-down time	t_{PD}	0	7	0	15	0	20	ns	
Write Operation									
Write cycle time	t_{WC}	12		15		20		ns	(Note 2)
Chip selection to end of write	t_{CW}	11		13		15		ns	
Address valid to end of write	t_{AW}	11		13		15		ns	
Address setup time	t_{AS}	0		0		0		ns	
Write pulse width	t_{WP}	10		12		14		ns	
Write recovery time	t_{WR}	0		0		0		ns	
Data valid to end of write	t_{DW}	7		7		8		ns	
Data hold time	t_{DH}	0		0		0		ns	
Write enable to output in high-Z	t_{WZ}	0	7	0	7	0	8	ns	(Note 4)
Output active from end of write	t_{OW}	0		0		0		ns	(Note 3)

Notes:

(1) Input pulse levels = GND to 3.0 V; input pulse rise and fall times = 5 ns; timing reference levels = 1.5 V; see figures 1 and 2 for output load.

(2) All read cycle timings are referenced from the last valid address to the first transitioning address.

(3) Transition is measured at ±200 mV from steady-state voltage with the loading shown in figure 2.

(4) Transition is measured at V_{OL} + 200 mV and V_{OH} − 200 mV with the loading shown in figure 2.

Figure 1. Output Load

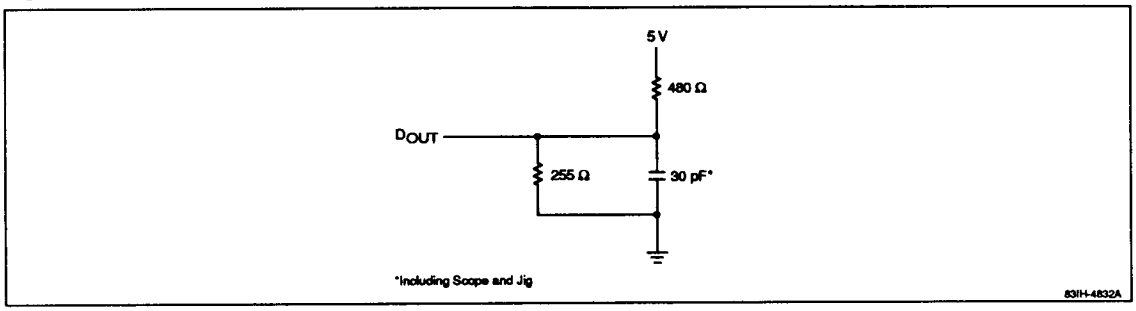
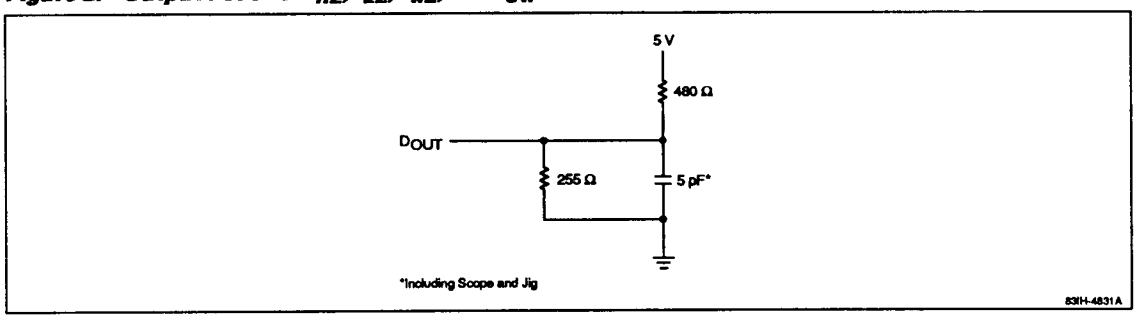
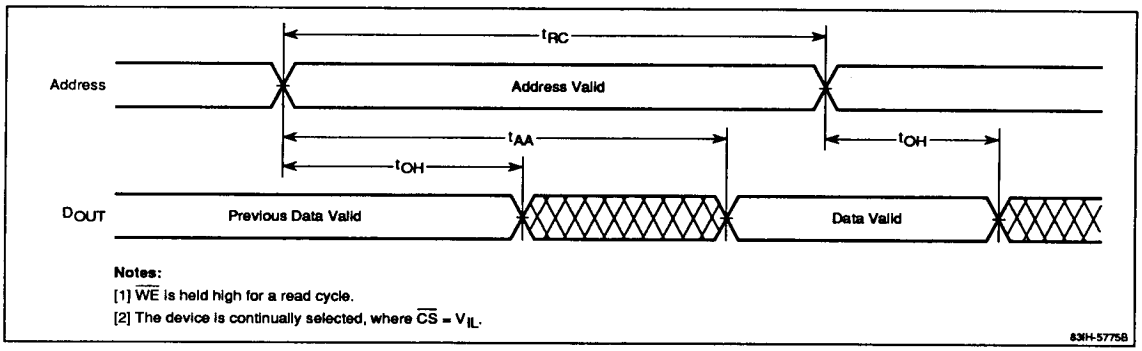


Figure 2. Output Load for t_{HZ}, t_{LZ}, t_{WZ}, and t_{OW}



Timing Waveforms

Address Access Cycle



Notes:
[1] $\overline{WE}$ is held high for a read cycle.
[2] The device is continually selected, where $\overline{CS}$ = V_{IL}.

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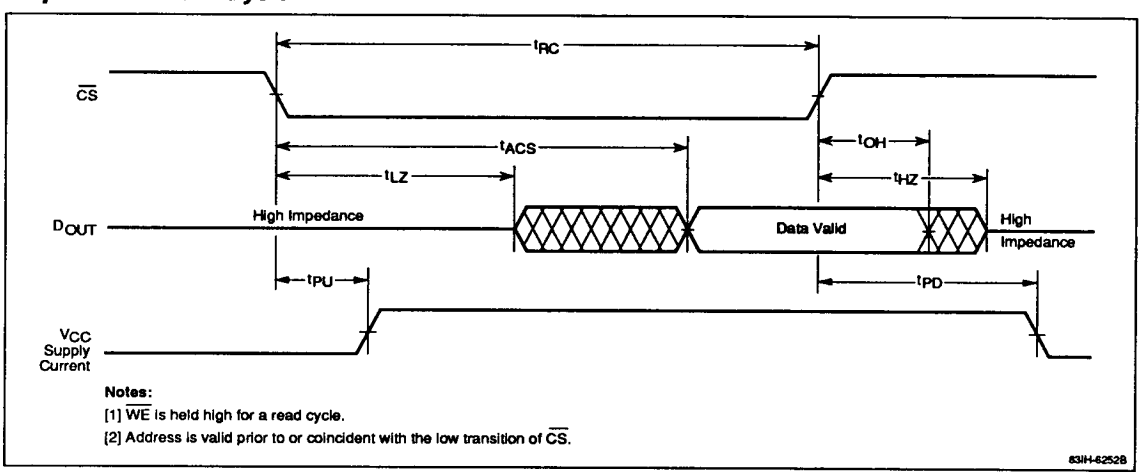
Chip Select Access Cycle



Notes:
[1] $\overline{WE}$ is held high for a read cycle.
[2] Address is valid prior to or coincident with the low transition of $\overline{CS}$.

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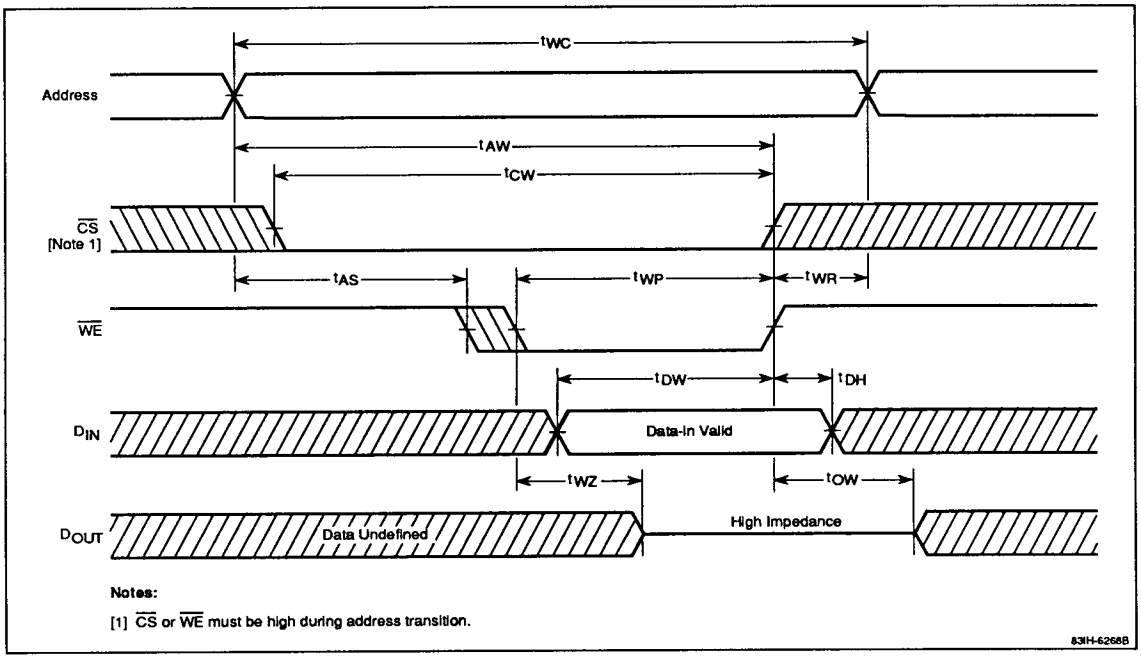
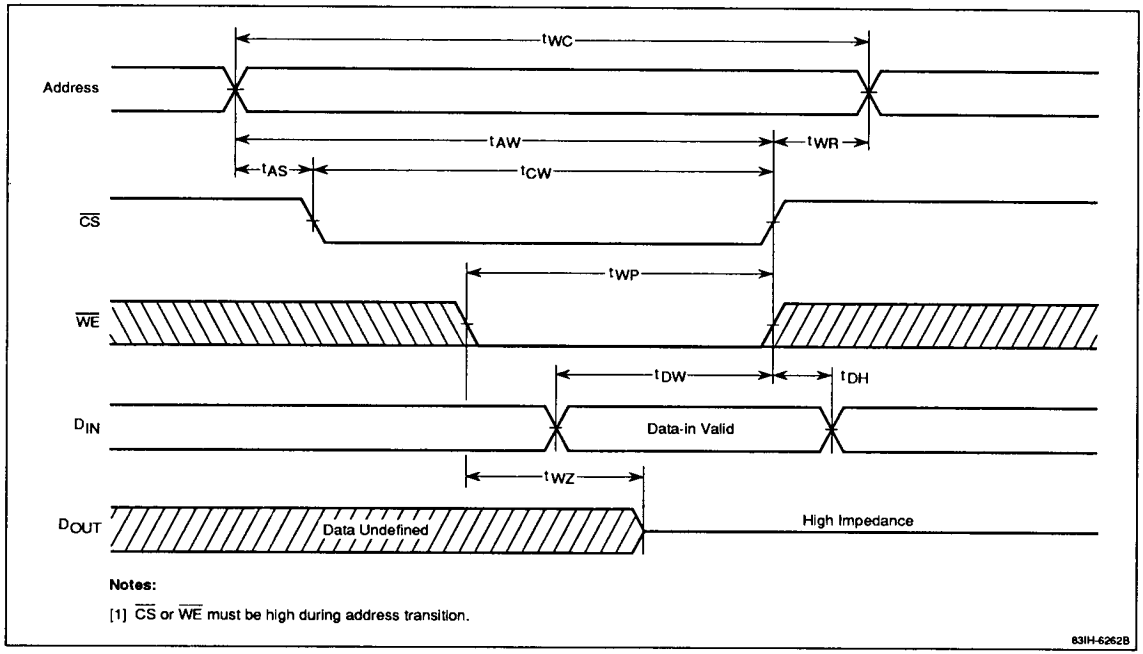
Timing Waveforms (cont)

WE-Controlled Write Cycle



Timing Waveforms (cont)

$\overline{CS}$-Controlled Write Cycle



Notes:

[1] $\overline{CS}$ or $\overline{WE}$ must be high during address transition.

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